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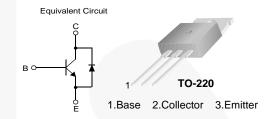


January 2016

KSC5603D NPN Silicon Transistor, Planar Silicon Transistor

Features

- High Voltage High Speed Power Switch Application
- · Wide Safe Operating Area
- · Built-in Free Wheeling Diode
- Suitable for Electronic Ballast Application
- Small Variance in Storage Time



Ordering Information

| Part Number | Marking | Package | Packing Method |
|-------------|---------|-----------|----------------|
| KSC5603DTU | C5603D | TO-220 3L | Rail |

Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at $T_A = 25^{\circ}\text{C}$ unless otherwise noted.

| Symbol | Parameter | Value | Unit |
|------------------|---|-------------|------|
| V_{CBO} | Collector-Base Voltage | 1600 | V |
| V _{CEO} | Collector-Emitter Voltage | 800 | V |
| V _{EBO} | Emitter-Base Voltage | 12 | V |
| I _C | Collector Current (DC) | 3 | Α |
| I _{CP} | Collector Current (Pulse) ⁽¹⁾ | 6 | Α |
| Ι _Β | Base Current (DC) | 2 | А |
| I _{BP} | Base Current (Pulse) ⁽¹⁾ | 4 | Α |
| P _C | Power Dissipation (T _C = 25°C) | 100 | W |
| T _J | Junction Temperature | 150 | °C |
| T _{STG} | Storage Temperature | -65 to +150 | °C |

Notes:

1. Pulse test: pulse width = 5 ms, duty cycle < 10%

Thermal Characteristics

Values are at $T_A = 25^{\circ}\text{C}$ unless otherwise noted.

| Symbol | Parameter | | Rating | Unit |
|----------------|--|---------------------|--------|------|
| $R_{	heta JC}$ | Thermal Resistance | Junction-to-Case | 1.25 | °C/W |
| $R_{	heta JA}$ | Thermal Nesistance | Junction-to-Ambient | 80 | °C/W |
| TL | Maximun Lead Temperatur : 1/8" from Case for 5 secon | • . | 270 | °C |

Electrical Characteristics

Values are at $T_A = 25$ °C unless otherwise noted.

| Symbol | Parameter | Conditions | | Min. | Тур. | Max. | Unit |
|-----------------------|--|---|------------------------|------|------|--|------|
| BV _{CBO} | Collector-Base Breakdown Voltage | $I_C = 0.5 \text{ mA}, I_E = 0$ | | 1600 | 1689 | | V |
| BV _{CEO} | Collector-Emitter Breakdown Voltage | $I_C = 5 \text{ mA}, I_B = 0$ | | 800 | 870 | | V |
| BV _{EBO} | Emitter-Base Breakdown Voltage | $I_E = 0.5 \text{ mA}, I_C = 0$ | | 12.0 | 14.8 | | V |
| I _{CES} | Collector Cut-Off Current | V _{CE} = 1600 V, V _{BE} = 0 | T _A = 25°C | | 0.01 | 100 | μΑ |
| | | | $T_A = 125^{\circ}C$ | | 0.04 | 100 1000 1000 1000 500 35 1.25 2.50 2.50 1.20 1.10 1.000 500 | |
| I _{CEO} | Collector Cut-Off Current | $V_{CE} = 800 \text{ V}, I_{B} = 0$ | | | 0.01 | | μΑ |
| | - W 0 0 0 0 0 | | I _A = 125°C | | | | |
| I _{EBO} | Emitter Cut-Off Current | $V_{EB} = 12 \text{ V}, I_{C} = 0$ | T | | 0.05 | | μΑ |
| | h _{FE} DC Current Gain | $V_{CE} = 3 \text{ V, } I_{C} = 0.4 \text{ A}$ | | 20 | 29 | 35 | |
| hee DC | | | | 6 | 15 | | |
| ''FE | Do danone dan | $V_{OF} = 10 \text{ V} \text{ Io} = 5 \text{ mA} $ | $T_A = 25^{\circ}C$ | 20 | 43 | | |
| | | | T _A = 125°C | 20 | 46 | | |
| | | $I_C = 250 \text{ mA}, I_B = 25 \text{ mA}$ | | | 0.50 | 1.25 | |
| V _{CE} (sat) | Collector-Emitter Saturation Voltage | $I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$ | | 1 | 1.50 | 2.50 | V |
| | voltago | $V_{EB} = 12 \text{ V, } I_{C} = 0$ $V_{CE} = 3 \text{ V, } I_{C} = 0.4 \text{ A}$ $V_{CE} = 10 \text{ V, } I_{C} = 5 \text{ mA}$ $I_{C} = 250 \text{ mA, } I_{B} = 25 \text{ mA}$ $I_{C} = 500 \text{ mA, } I_{B} = 50 \text{ mA}$ $I_{C} = 1 \text{ A, } I_{B} = 0.2 \text{ A}$ $I_{C} = 500 \text{ mA, } I_{B} = 50 \text{ mA}$ $I_{C} = 24 \text{ A, } I_{C} = 0.4 \text{ A}$ $I_{C} = 24 \text{ A, } I_{C} = 0.4 \text{ A}$ $V_{CE} = 10 \text{ V, } I_{C} = 0, f = 1 \text{ MHz}$ | | | 1.20 | 2.50 | |
| | | I 500 A I 50 A | T _A = 25°C | | 0.74 | 4.8 .01 | V |
|) | Base-Emitter Saturation | $I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$ | T _A = 125°C | | 0.61 | | |
| V _{BE} (sat) | Voltage | I _C = 2 A, I _B = 0.4 A | T _A = 25°C | | 0.85 | 1.20 | |
| | | | T _A = 125°C | | 0.74 | 1.10 | |
| C _{ib} | Input Capacitance | | | | 745 | 1000 | pF |
| C _{ob} | Output Capacitance | V _{CB} = 10 V, I _E = 0, f = 1 MHz | | | 56 | 500 | pF |
| f _T | Current Gain Bandwidth Product | I _C = 0.1 A,V _{CE} = 10 V | | | 5 | | MHz |
| | D: 1 E 1)//// | I _F = 0.4 A | | | 0.76 | 1.20 | ., |
| V _F | Diode Forward Voltage | I _F = 1 A | | | 0.83 | 1.50 | V |

Electrical Characteristics (Continued)

Values are at $T_A = 25^{\circ}C$ unless otherwise noted.

| Symbol | Parameter | Conditions | Min. | Тур. | Max. | Unit | |
|---|-----------------|--|------|------|------|------|--|
| RESISTIVE LOAD SWITCHING (D.C ≤ 10%, Pulse Width = 20 μs) | | | | | | | |
| t _{ON} | Turn-On Time | $I_C = 0.3 \text{ A}, I_{B1} = 50 \text{ mA},$ | | 400 | 600 | ns | |
| t _{STG} | Storage Time | $I_{B2} = 150 \text{ A}, V_{CC} = 125 \text{ V},$ | 2.0 | 2.1 | 2.3 | μs | |
| t _F | Fall Time | $R_L = 416 \Omega$ | | 310 | 1000 | ns | |
| t _{ON} | Turn-On Time | $I_C = 0.5 \text{ A}, I_{B1} = 50 \text{ mA},$ | | 600 | 1100 | ns | |
| t _{STG} | Storage Time | $I_{B2} = 250 \text{ mA}, V_{CC} = 125 \text{ V},$ | | 1.3 | 1.5 | μs | |
| t _F | Fall Time | $R_L = 250 \Omega$ | | 180 | 350 | ns | |
| INDUCTIVE LOAD SWITCHING (V _{CC} = 15 V) | | | | | | | |
| t _{STG} | Storage Time | $I_C = 0.3 \text{ A}, I_{B1} = 50 \text{ mA},$ | 0.60 | 0.73 | 0.90 | μs | |
| t _F | Fall Time | $I_{B2} = 150 \text{ mA}, V_Z = 300 \text{ V},$ $L_C = 200 \text{ H}$ | | 170 | 250 | ns | |
| t _C | Cross-Over Time | | | 180 | 250 | ns | |
| t _{STG} | Storage Time | I _C = 0.5 A, I _{B1} = 50 mA, | 0.70 | 0.84 | 1.00 | μs | |
| t _F | Fall Time | $I_{B2} = 250 \text{ mA}, V_Z = 300 \text{ V},$ $L_C = 200 \text{ H}$ | | 140 | 175 | ns | |
| t _C | Cross-Over Time | | | 170 | 200 | ns | |

Typical Performance Characteristics

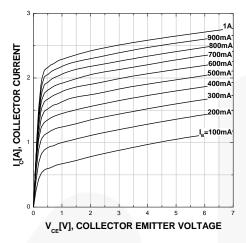


Figure 1. Static Characteristic

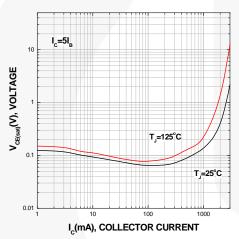


Figure 3. Collector-Emitter Saturation Voltage

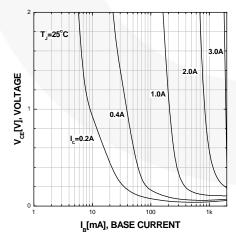


Figure 5. Typical Collector Saturation Voltage

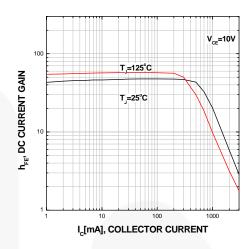


Figure 2. DC Current Gain

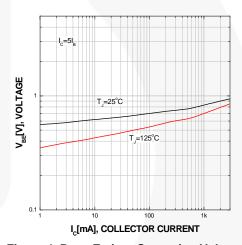
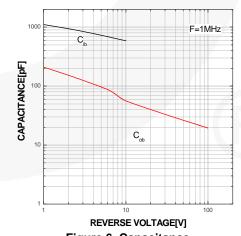


Figure 4. Base-Emitter Saturation Voltage



Typical Performance Characteristics (Continued)

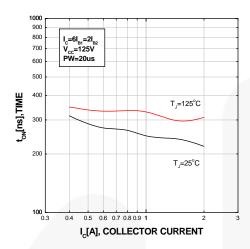


Figure 7. Resistive Switching Time, ton

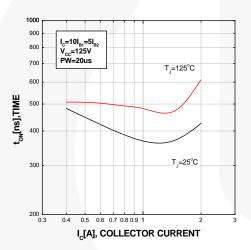


Figure 9. Resistive Switching Time, ton

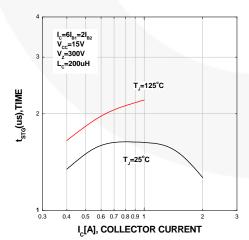


Figure 11. Inductive Switching Time, t_{STG}

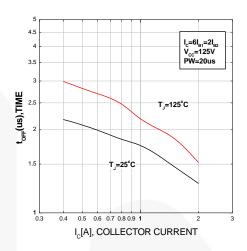


Figure 8. Resistive Switching Time, toff

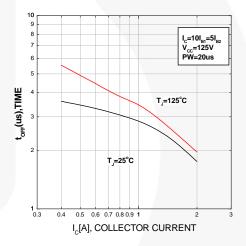


Figure 10. Resistive Switching Time, toff

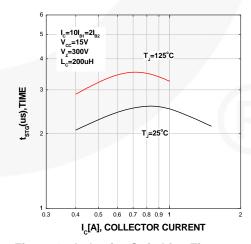


Figure 12. Inductive Switching Time, t_{STG}

Typical Performance Characteristics (Continued)

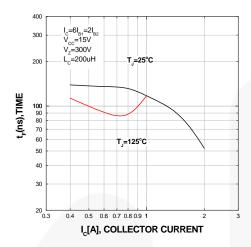


Figure 13. Inductive Switching Time, t_F

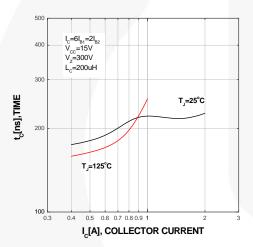


Figure 15. Inductive Switching Time, t_c

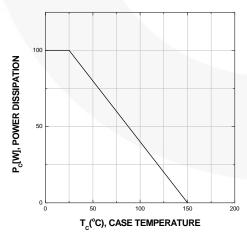


Figure 17. Power Derating

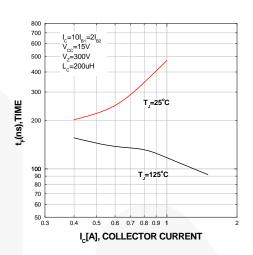


Figure 14. Inductive Switching Time, t_F

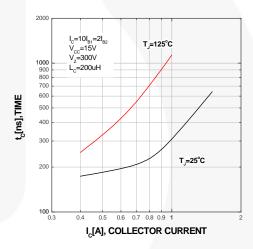
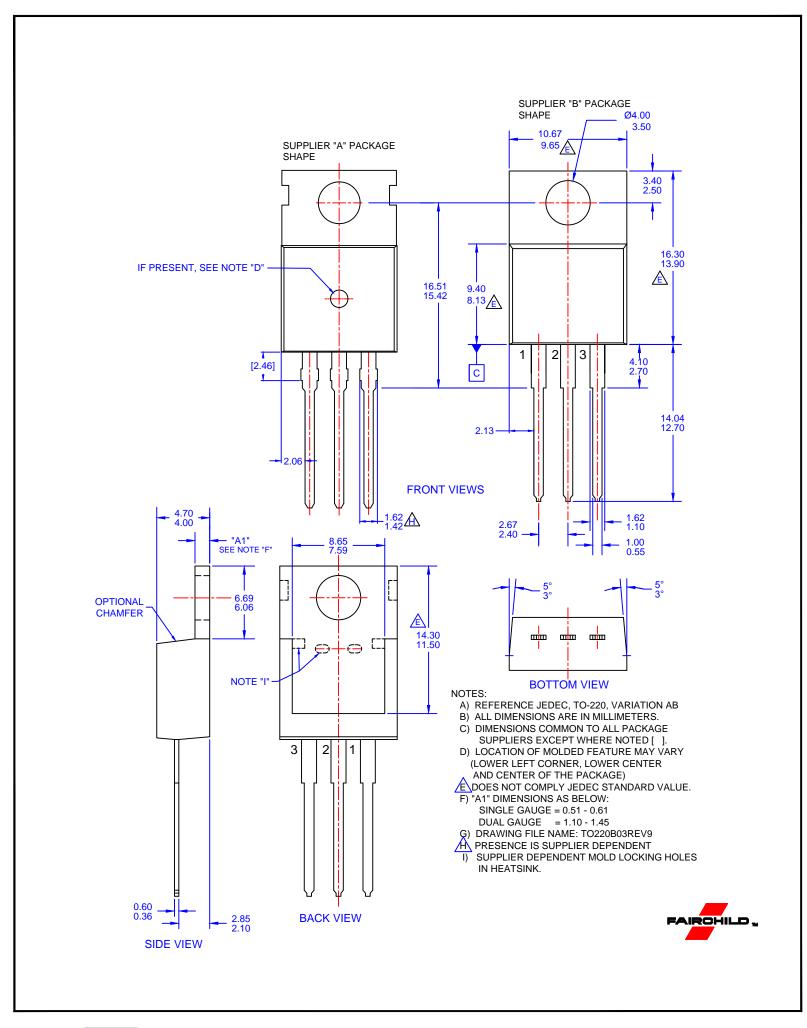


Figure 16. Inductive Switching Time, t_c



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